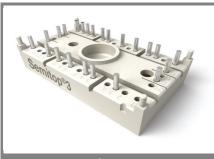
## **SK 70 DH**



SEMITOP® 3

# Half Controlled Bridge Rectifier

#### **SK 70 DH**

**Preliminary Data** 

#### **Features**

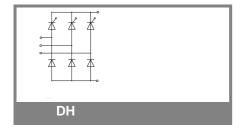
- Compact design
- · One screw mounting
- Heat transfer and insolation through direct copper bonded aluminium oxide ceramic (DBC)
- Glass passived thyristor chips
- Up to 1600V reverse voltage
- UL recognized, file no. E 63 532

### **Typical Applications**

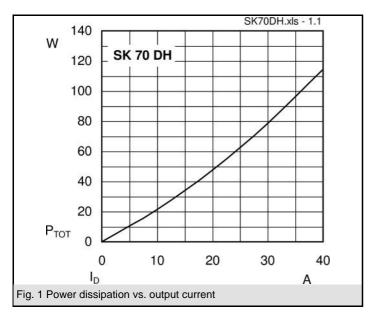
- Soft starters
- Light control
- · Temperature control
- Motor control

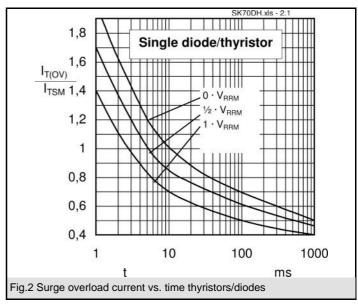
V <sub>RSM</sub>	V <sub>RRM</sub> , V <sub>DRM</sub>	$I_D = 68 \text{ A (full conduction)}$
V	V	$(T_S = 80 \text{ °C)}$
900	800	SK 70 DH 08
1300	1200	SK 70 DH 12
1700	1600	SK 70 DH 16

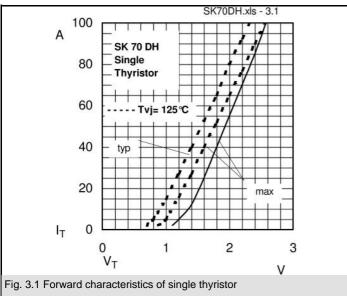
Symbol	Conditions	Values	Units
$I_D$	T <sub>s</sub> = 80 °C	68	Α
I <sub>FSM</sub> / I <sub>TSM</sub>	T <sub>vi</sub> = 25 °C; 10 ms	370	Α
	$T_{vj} = 125 ^{\circ}\text{C}; 10 \text{ms}$	270	Α
i²t	$T_{vj} = 25  ^{\circ}\text{C}; 10  \text{ms}$	685	A²s
	$T_{vj} = 125 ^{\circ}\text{C}; 10 \text{ms}$	365	A²s
V <sub>T</sub>	T <sub>vj</sub> = 25 °C; 75A	max. 1,9	V
$V_{T(TO)}$	$T_{vj} = 125 ^{\circ}C;$	max. 1	V
r <sub>T</sub>	$T_{vj} = 125  ^{\circ}C$	max. 10	mΩ
I <sub>DD</sub> ; I <sub>RD</sub>	$T_{vj}$ = 125 °C; $V_{DD}$ = $V_{DRM}$ ; $V_{RD}$ = $V_{RRM}$	max. 10	mA
t <sub>gd</sub>	$T_{vj} = 25 \text{ °C; } I_G = 1 \text{ A; } di_G/dt = 1 \text{ A/}\mu\text{s}$	1	μs
t <sub>gr</sub>	$V_D = 0.67 \cdot V_{DRM}$	2	μs
(dv/dt) <sub>cr</sub>	T <sub>vj</sub> = 125 °C	max. 1000	V/µs
(di/dt) <sub>cr</sub>	T <sub>vj</sub> = 125 °C; f = 5060 Hz	max. 50	A/µs
t <sub>q</sub>	$T_{vj} = 125 ^{\circ}\text{C}$ ; typ.	120	μs
I <sub>H</sub>	$T_{vj} = 25 ^{\circ}\text{C}$ ; typ. / max.	80 / 150	mA
IL	$T_{vj}$ = 25 °C; $R_G$ = 33 $\Omega$	150 / 300	mA
V <sub>GT</sub>	T <sub>vi</sub> = 25 °C; d.c.	min. 2	V
I <sub>GT</sub>	$T_{vi} = 25  ^{\circ}\text{C}; \text{d.c.}$	min. 100	mA
$V_{GD}$	$T_{vj} = 125 ^{\circ}\text{C}; \text{d.c.}$	max. 0,25	V
$I_{GD}$	$T_{vj} = 125 ^{\circ}\text{C}; \text{d.c.}$	max. 3	mA
Rth(j-s)	Per thyristor	1,2	K/W
	Per diode	1,7	K/W
T <sub>solder</sub>	Terminals, 10s	260	°C
T <sub>vi</sub>	Diodes	-40+150	°C
$T_{vj}$			°C
T <sub>stg</sub>		-40+125	°C
$T_{vj}$	Thyristors	-40+125	°C
V <sub>isol</sub>	a. c. 50 Hz; r.m.s.; 1 s / 1 min.	3000 ( 2500 )	V
M <sub>s</sub>	Mounting torque to heatsink	2,5	Nm
m	weight	30	g
Case	SEMITOP® 3	T 40	

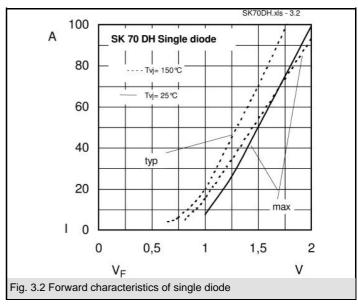


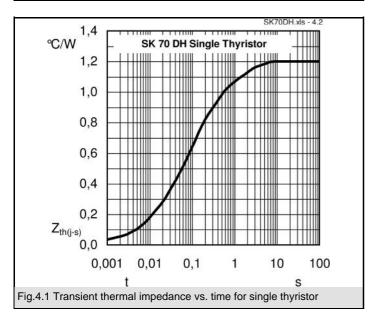
## **SK 70 DH**

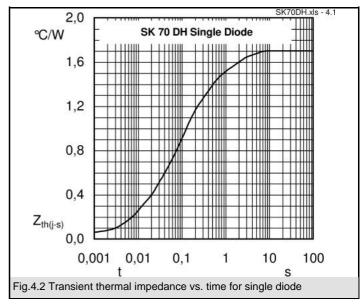


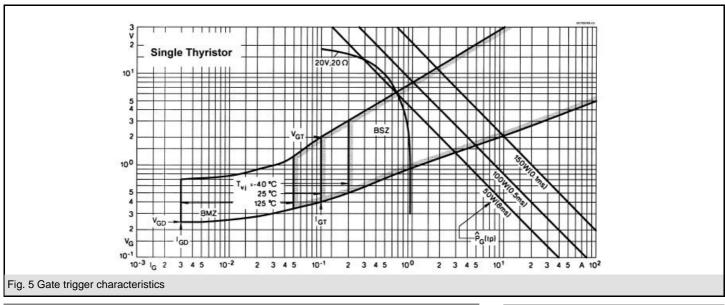


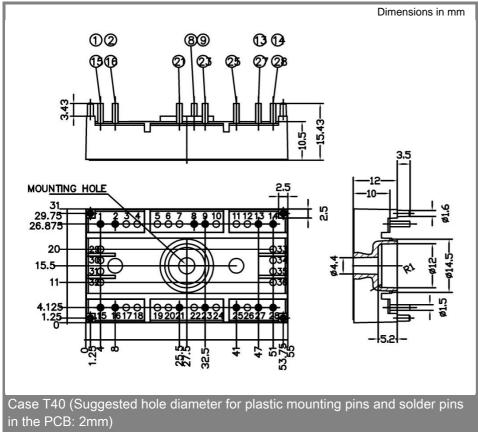


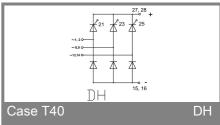












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